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INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicati n Number	10/043065
(Use as many sheets as necessary)	Filing Date	January 9, 2002
IPE	First Named Inventor	Forbes, Leonard
01. 40	Group Art Unit	2822
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Sheet 1 of 1	Attorney Docket No: 3	03.684US3
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	MADE		ATENT DOCUMENT	S		
Examiner Initial	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
KK.	US-5,852,311	12/22/1998	Kwon, et al.			06/05/1997
VV.	US-5,869,370	02/09/1999	Chuang, et al.	438	264	12/29/1997

		<b>FOREIGN PATENT</b>	DOCUMENTS			
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	7

	OTHER	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No '	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the Item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-lasue number(s),	1,
MANAGE		publisher, city and/or country where published.	į .

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Substitute for form 1449A/PTO	Complete if Known	required to respond to a collection of information unless it contains a valid OMB control number.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Application Number	10/043065
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Use as many sneets as necessary)	First Named Inventor	Forbes, Leonard
( JUN 0 1 2004 gg	Group Art Unit	2822
Jun 0 1 2	Examiner Name	Rose, Kiesha
Sheet 1 of 1	Attorney Docket No: 3	03.684US3

		US P	ATENT DOCUMENT	S		
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
VI.	US-6,297,103	10/02/2001	Ahn, Kie, et al.	438	275	02/28/2000
7	US-6,456,535	09/24/2002	Forbes, L., et al.	365	185.28	06/15/2001
	US-6,605,961	08/12/2003	Forbes, L.	326	41	02/29/2000
	US-6,639,835	10/28/2003	Forbes, L.	365	186.14	02/29/2000
1/2	US-6,720,221	04/13/2004	Ahn, Kie, et al.	438	275	08/30/2001
VV	US-6,730,960	05/04/2004	Forbes, L.	257	321	08/30/2001

EXAMINER

DATE CONSIDERED

PTO/S9/084(10-01)
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/043065
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02	First Named Inventor	Forbes, Leonard
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MAR 1 7 2004 2	Examiner Name	Rose, Kiesha
Sheet 1 of 2	Attorney Docket No: 3	803.684US3
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		US PA	ATENT DOCUMENT	S		
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
KR	US- 2002/0016081 A1	02/07/2002	Aloni, E., et al.	438	714	10/15/2001
	US- 2003/0001197	01/02/2003	Chang, Y., et al.	257	315	08/30/2002
	US- 2003/0201491	10/30/2003	Chung, B.	257	324	05/08/2003
	US-5,408,115	04/18/1995	Chang, K.	257	324	04/04/1994
	US-5,852,306	12/22/1998	Forbes, Leonard	257	315	01/29/1997
	US-5,959,896	09/28/1999	Forbes, L.	365	185.33	02/27/1998
	US-5,989,958	11/23/1999	Forbes, Leonard	438	257	08/20/1998
	US-6,100,559	08/08/2000	Park,	257	315	08/14/1998
	US-6,222,224	04/24/2001	Shigyo, N.	257	315	12/19/1997
1	US-6,245,613	06/12/2001	Hsu, , et al.			04/24/2000
Ī	US-6,246,089	06/12/2001	Lin, Yai-Fen, et al.	257	315	03/13/2000
	US-6,265,266	07/24/2001	Dejenfelt, A. T., et al.	438	258	09/27/1996
	US-6,316,316	11/13/2001	Wu, S.	438	260	06/18/1999
ı	US-6,351,428	02/26/2002	Forbes, Leonard	365	230.06	02/29/2000
	US-6,383,939	05/07/2002	Yang, W., et al.	438	706	08/17/1999
	US-6,515,328	02/04/2003	Yang, W., et al.	257	315	02/04/1999
ZJZ	US-6,583,011	06/24/2003	Xia, L., et al.	438	275	01/11/2000

		<b>FOREIGN PATENT</b>	DOCUMENTS			
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T²

	OTHE	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
KR		CHAU, R., et al., "30nm Physical Gate Length CMOS Tansistors with 1.0 ps n-MOS and 1.7 ps p-MOS Gate Delays", <u>IEEE Int. Electron, Devices Meeting, San Francisco</u> , (December, 2000),pp. 45-48	
		FRANK, J., et al., "Monte Carlo Simulations of p- and n-Channel Dual-Gate Si MOSFET's at the Limits of Scaling", <u>IEEE Transactions on Electron Devices</u> , 40(11), (November 1993),pg. 2103	
		HIRAYAMA, M., et al., "Low-Temperature Growth of High-Integrity Silicon Oxide Films by Oxygen Radical Generated in High-Density Krypton Plasma", IEEE, (1999),4 pages	
KR		ILYAS, M., et al., "The optical absorption edge of amorphous thin films of silicon monoxide and of silicon monoxide mixed with titanium monoxide", IEE, (2001),1	

EXAMINER DATE CONSIDERED 11/2/04

PTO/SB/08A(10-01)
Approved for use through 10/31/2022, CMB 651-0031
US Patent & Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO	Complete if Known	required to respond to a collection of information unless it contains a valid CMS control number
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/043065
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	First Named Inventor	Forbes, Leonard
MAR 1 7 2004 (5)	Group Art Unit	2822
MAR 13	Examiner Name	Rose, Kiesha
Sheet 2 of 20 PACE: is co	Attorney Docket No: 3	03.684US3

	OTHE	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T
140		page	
KK		MULLER, D. A., "The Electronic Structure at the Atomic Scale of Ultrathin Gate Oxides", Nature, 399, (June 1999),758-761	
		OHGURO, T., "Tenth Micron P-MOSFET's with Ultra-Thin Epitaxial Channel Layer Grown by Ultra-High-Vacuum CVD", Proceedings: International Electron Devices Meeting, IEEE, Washington, Dec. 5-8, 1993, (Dec. 5, 1993), pp. 433-436	
		STRASS, A., et al., "Fabrication and Characterisation of thin low-temperature MBE-compatible silicon oxides of different stoichiometry", <u>Thin Solid Films 349</u> , (1999),pp. 135-146	
KR		TIWARI, SANDIP, "Volatile and Non-Volatile Memories in Silicon with Nano-Crystal Storage", Int'l Electron Devices Meeting: Technical Digest, Washington, DC,(Dec. 1995),521-524	

EXAMINER OUL

DATE CONSIDERED

11/2/04

Substitute Disclosure Statement Form (PTO-1449)

- EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional) a Applicant is to place a check mark here if English language Transitation is attached

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	Application Numb r	10/043065		
	Filing Date	January 9, 2002		
	First Named Inv ntor	Forbes, Leonard		
	Gr up Art Unit	2822		
	Examiner Name	Rose, Kiesha		
Sheet 1 of 2	Attorney Docket No: 303.684US3			

		US PA	TENT DOCUMENT	S		
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	US- 2002/0016081 A1	02/07/2002	Aloni, E. , et al.	438	714	10/15/2001
	US- 2003/0001197	01/02/2003	Chang, Y., et al.	257	315	08/30/2002
	US- 2003/0201491	10/30/2003	Chung, B.	257	324	05/08/2003
	US-5,408,115	04/18/1995	Chang, K.	257	324	04/04/1994
	US-5,852,306	12/22/1998	Forbes, Leonard	257	315	01/29/1997
	US-5,959,896	09/28/1999	Forbes, L.	365	185.33	02/27/1998
	US-5,989,958	11/23/1999	Forbes, Leopard	438	257	08/20/1998
	US-6,100,559	08/08/2000 \ /	Park/	257	315	08/14/1998
	US-6,222,224	04/24/2001	Shigyo, M.	257	315	12/19/1997
	US-6,245,613	06/12/2001	∕Hsu, √et al.			04/24/2000
	US-6,246,089	06/12/200/(\	Lin, Yai-Fen, et al.	257	315	03/13/2000
	US-6,265,266	07/24/2001	Defenfelt, A. T., et al.	438	258	09/27/1996
	US-6,316,316	11/13/2001/	y∜u, S.	438	260	06/18/1999
	US-6,351,428	Q2/26/2992	Forbes, Leonard	365	230.06	02/29/2000
	US-6,383,939	05/07/2002	Yang, W., et al.	438	706	08/17/1999
	US-6,515,328	(02)04/2003	Yang, W., et al.	257	315	02/04/1999
	US-6,583,011	06/24/2003/	Xia, L., et al.	438	275	01/11/2000

	7	Q	FO	REIGN PATENT	DOCUMENTS			
Examiner initials*	Foreign Docu	ment No	X	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>

	OTHE	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No 1	inclúde name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T.
		CHAU, R., et al., "30nm Physical Gate Length CMOS Tansistors with 1.0 ps n-MOS and 1.7 ps p-MOS Gate Delays", [EEE Int. Electron, Devices Meeting, San Francisco, (December, 2000),pp. 45-48	
		FRANK, J., et al., "Monte Carlo Simulations of p- and n-Channel Dual-Gate Si MOSFET's at the Limits of Scaling", IEEE Transactions on Electron Devices, 40(11), (November 1993),pg. 2103	
		HIRAYAMA, M., et al., "Low-Temperature Growth of High-Integrity Silicon Oxide Films by Oxygen Radical Generated in High-Density Krypton Plasma", IEEE, (1999),4 pages	
		ILYAS, M., et al., "The optical absorption edge of amorphous thin films of silicon monoxide and of silicon monoxide mixed with titanium monoxide", IEE, (2001),1	

EXAMINER

DATE CONSIDERED

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Substitute for form 1449VPTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many strong by recording)	Under the Presentation for all IRA to present a require to a constitution of intervious present a constitution of control presents and the control presents of the control pre			
	<b>Application Number</b>	10/043065 January 9, 2002 Forbes, Leonard		
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	Group Art Unit	2822		
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Sheet 2 of 20 PACETIVE DO	Attorney Docket No: 3	003.684US3		

	OTHE	R DOCUMENTS - NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No '	include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine journal, serial, symposium, catalog, etc.), data, page(s), volume-issue number(s), publisher, city and/or country where published.	77
		page \ \	
		MULLER, D.A., "The Electronic Structure at the Atomic Scale of Ultrathin Gate Oxides", Nature, 399, (June 1999),758-761	
		OHG IBO, T., "Tenth Micron P-MOSFET's with Ultra-Thin Epitaxial Channel Layer From by Ultra-High-Vacuum CVD", Proceedings: International Electron Devices Meeting, IEEE, Washington, Dec. 5-8, 1993, (Dec. 5, 1993), pp. 433-436	
		STRASS, A , et al., "Fabrication and Characterisation of thin low-temperature MBE-compatible silicon oxides of different stoichiometry", Thin Solid Films 349, (1999), pp. 135-146	
,		TIWARI, SANDIP, "Volatile and Non-Volatile Memories in Silicon with Nano-Corstal Storage", Int'l Electron Devices Meeting: Technical Digest, Washington, DC,(Dec. 1995),521-524	

**EXAMINER**